

FIG. 1 (PRIOR ART)

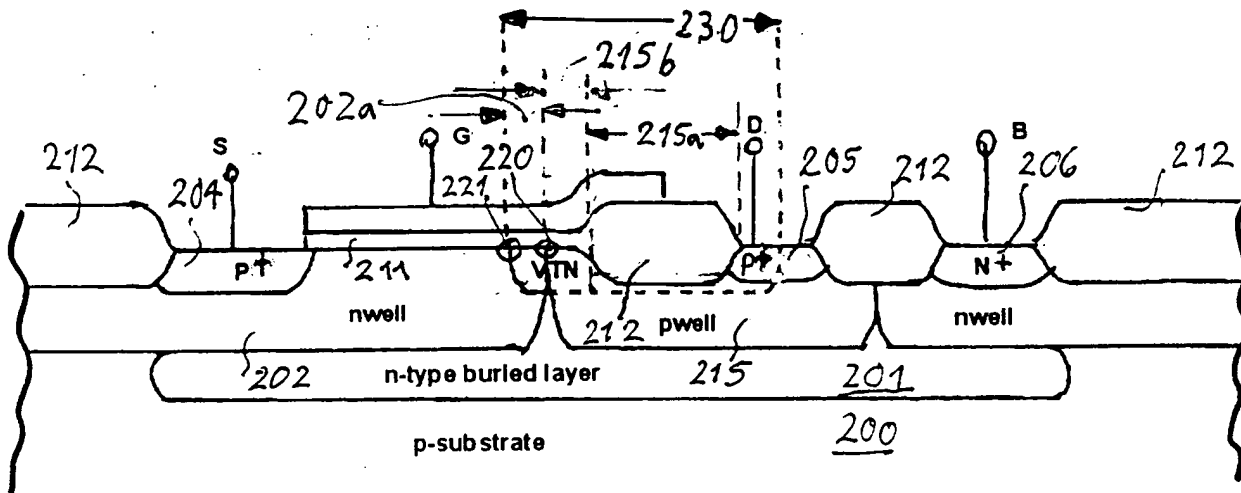


FIG. 2

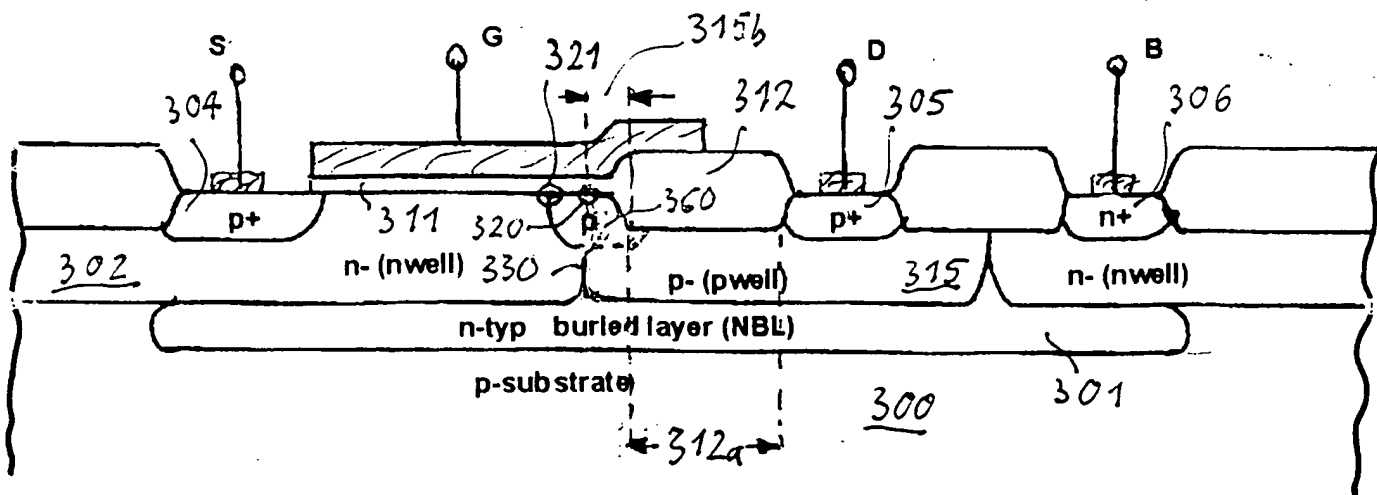


FIG. 3

401 ~ Begin

400

402 ~

Providing a ^{first} well of a first conductivity type, operable as the extension of the transistor drain of the first conductivity type and covered by a first insulator having a first thickness, and a ^{second} well of the opposite conductivity type, intended to contain the transistor source of the first conductivity type and covered by a second insulator thinner than the first insulator, the first and second wells forming a junction that terminates at the second insulator

403 ~

Depositing a photoresist layer over the wafer

404 ~

Patterning the photoresist layer by opening a window laterally extending from the drain to the junction termination

405 ~

Implanting ions of the first conductivity type through the window into the first well, the ions having an energy to limit the penetration ^{depth} to the first insulator thickness, and a dose to create a well region of high doping concentration adjacent to the junction termination

406 ~ End

FIG. 4

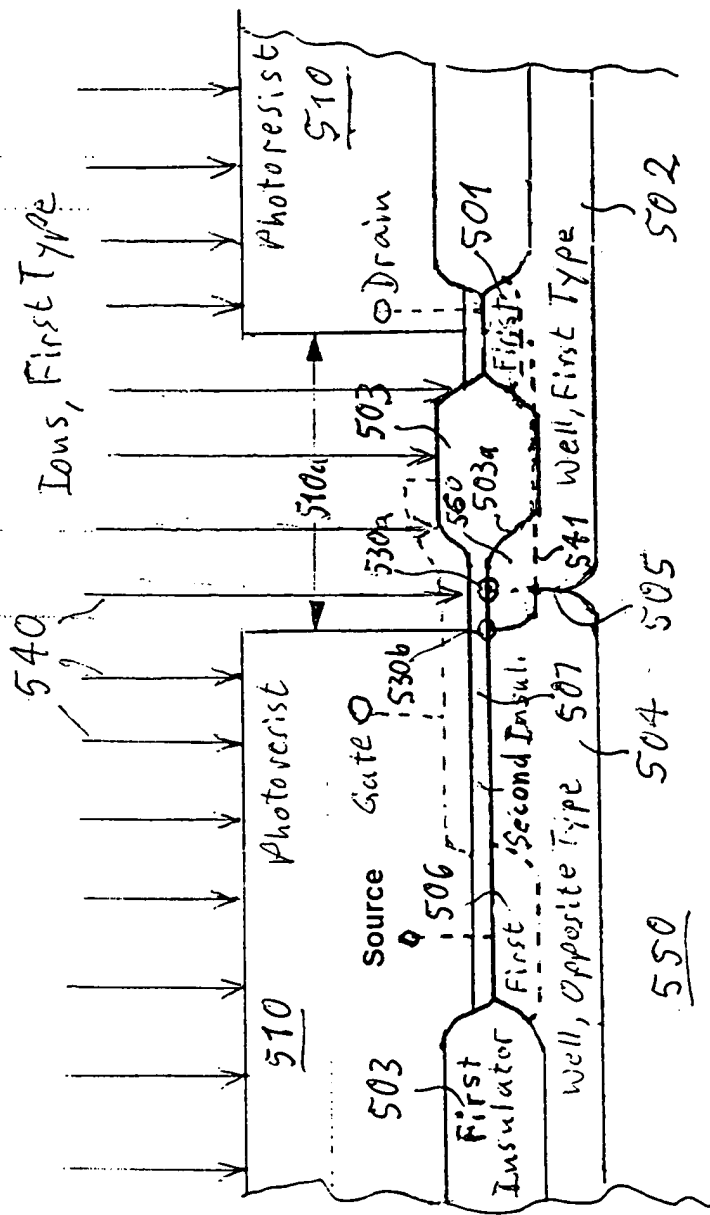
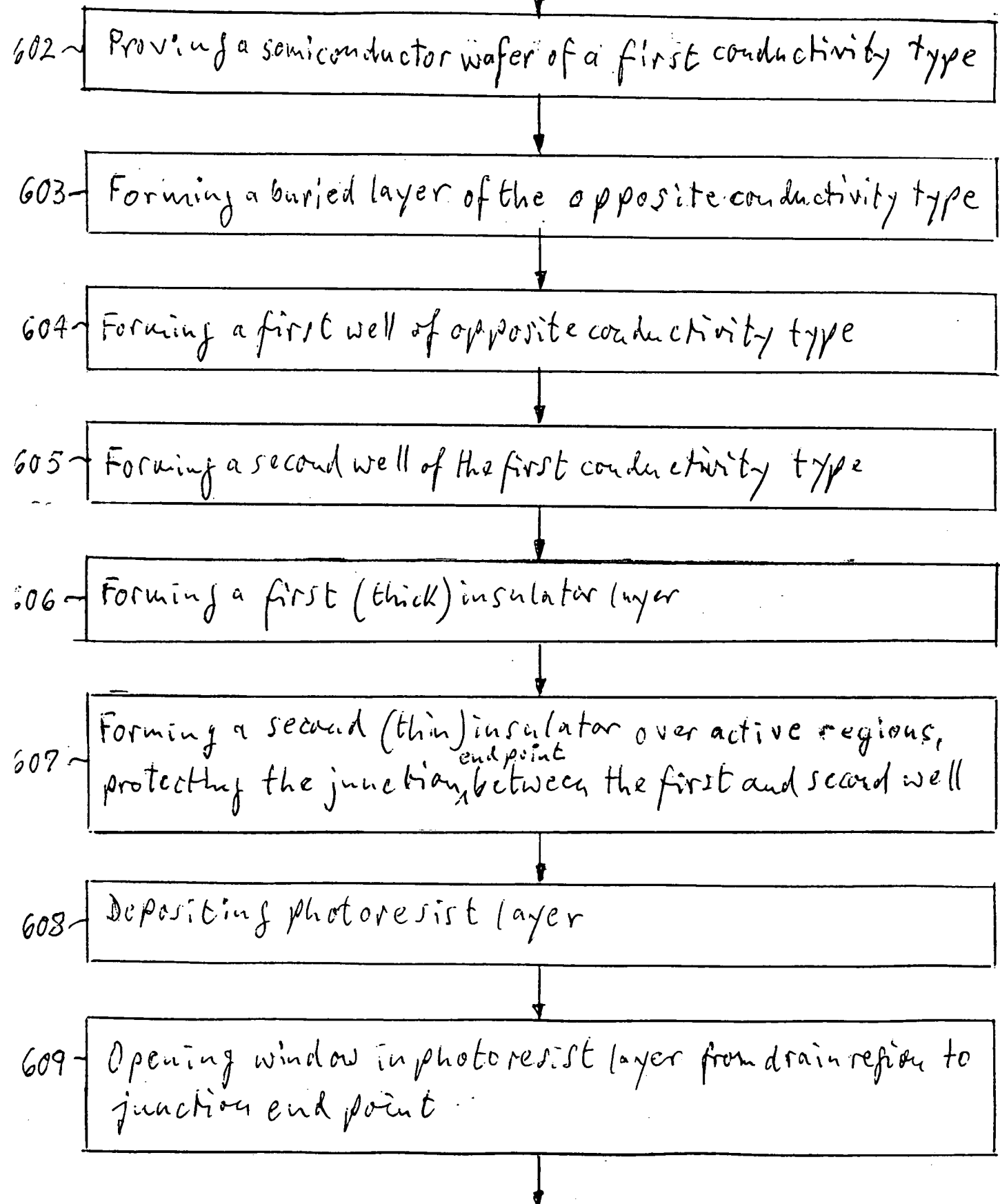


FIG. 5

600

601~ Begin



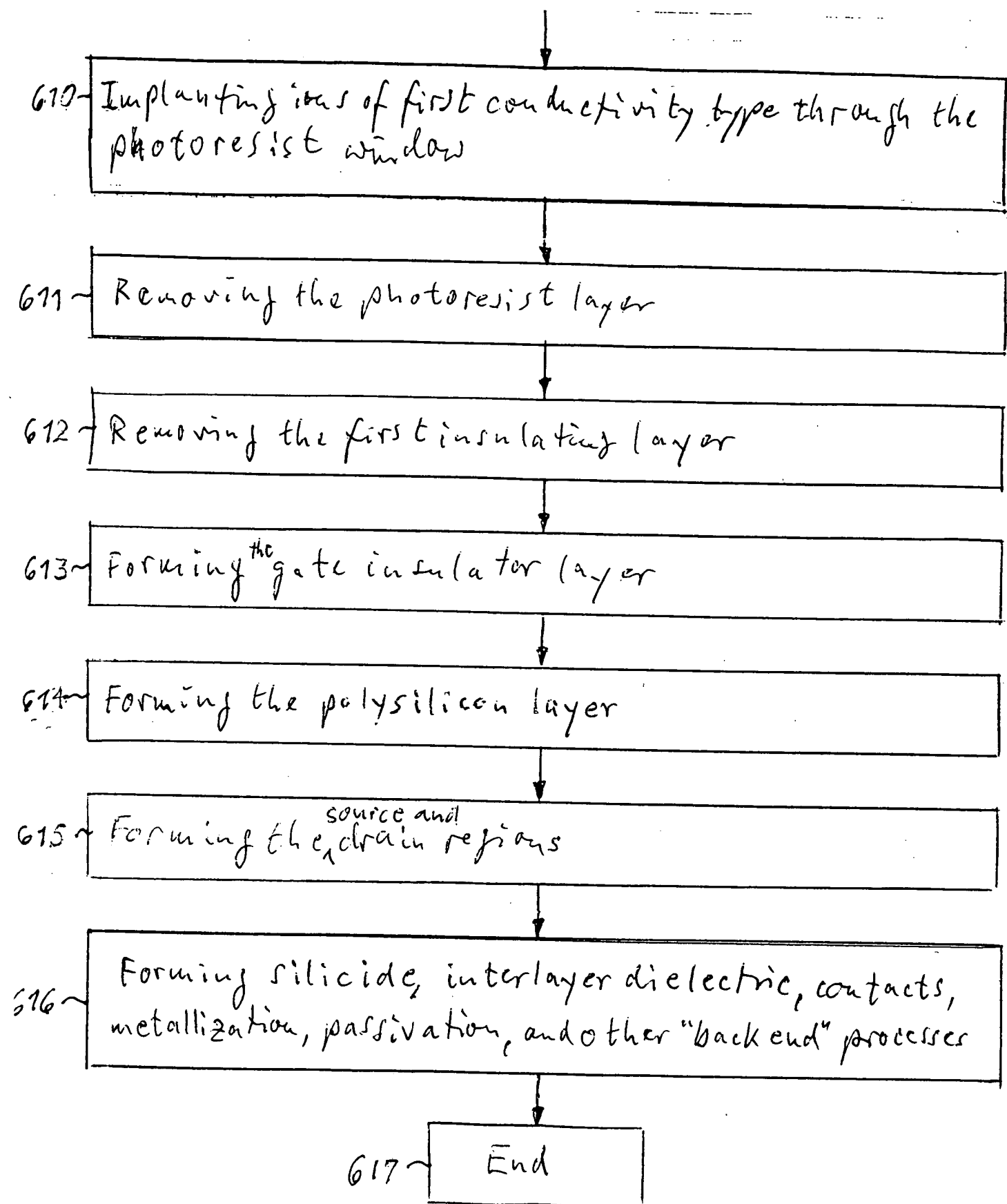


FIG. 6

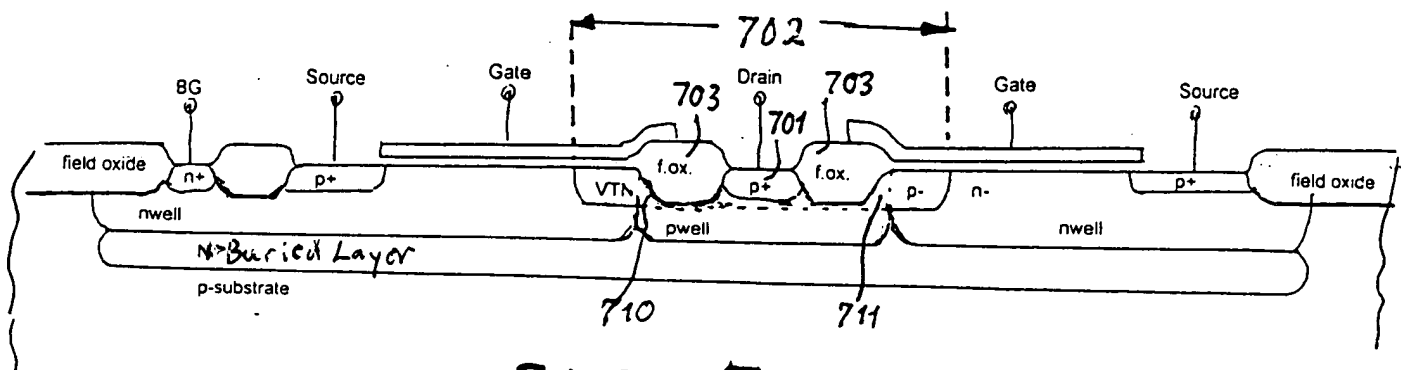


FIG. 7

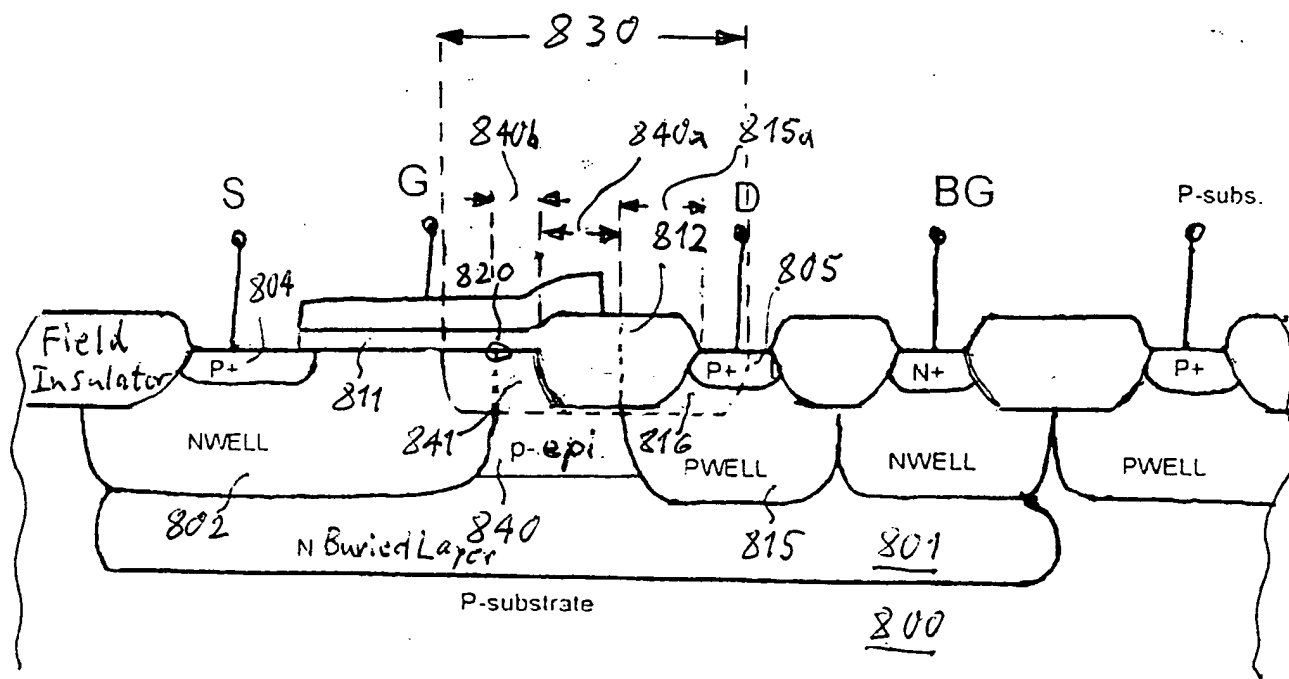


FIG. 8

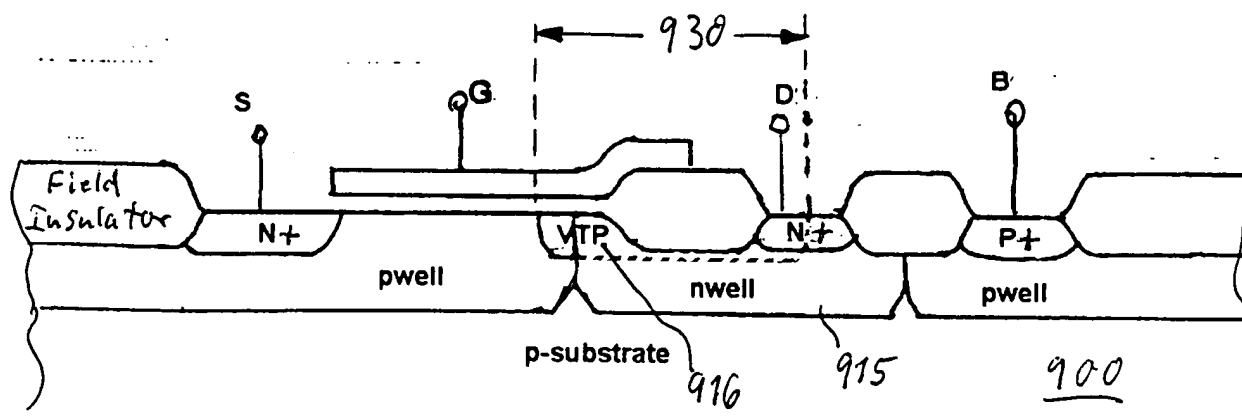


FIG. 9

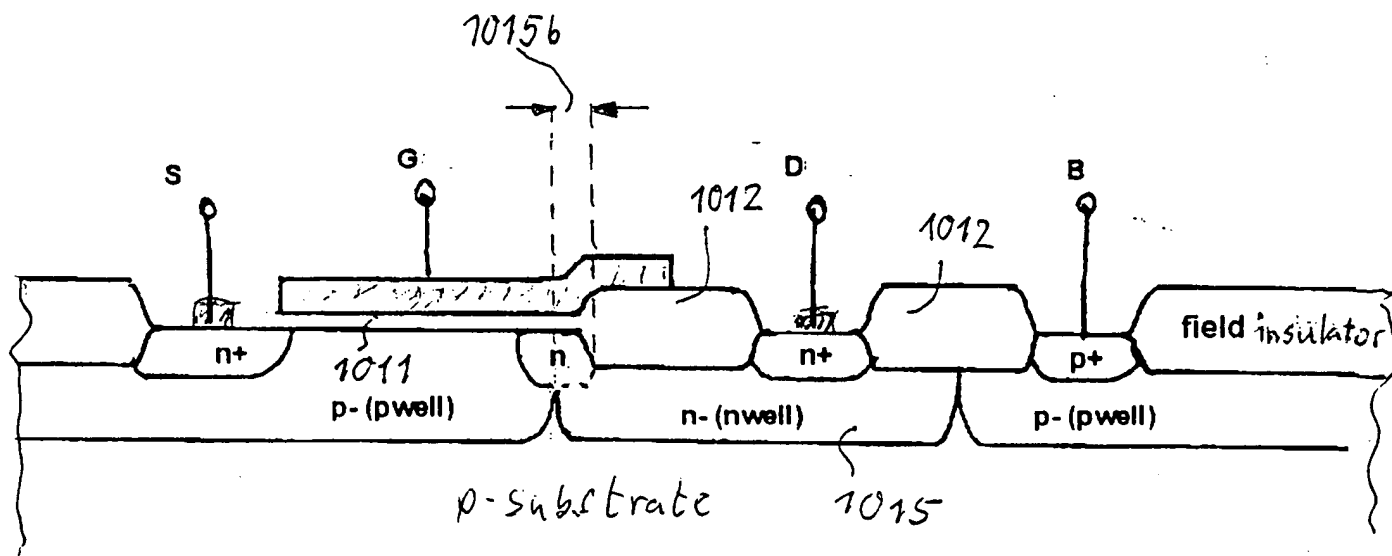


FIG. 10